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Understanding [Embedded - DSP \(Digital Signal Processors\)](#)

[Embedded - DSP \(Digital Signal Processors\)](#) are specialized microprocessors designed to perform complex mathematical computations on digital signals in real-time. Unlike general-purpose processors, DSPs are optimized for high-speed numeric processing tasks, making them ideal for applications that require efficient and precise manipulation of digital data. These processors are fundamental in converting and processing signals in various forms, including audio, video, and communication signals, ensuring that data is accurately interpreted and utilized in embedded systems.

Applications of [Embedded - DSP \(Digital Signal Processors\)](#)

Details

Product Status	Obsolete
Type	SC1400 Core
Interface	Host Interface, I ² C, UART
Clock Rate	266MHz
Non-Volatile Memory	External
On-Chip RAM	80kB
Voltage - I/O	3.30V
Voltage - Core	1.20V
Operating Temperature	-40°C ~ 105°C (TJ)
Mounting Type	Surface Mount
Package / Case	400-LFBGA
Supplier Device Package	400-LFBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/msc7110vm1000

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Bottom View

	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1
A	NC	NC	NC	NC	NC	GND	HD0	HD1	HD4	HD6	HD7	HD10	HD12	HD15	$\overline{\text{CK}}$	CK	DQS2	DQM1	GND	GND
B	NC	NC	NC	NC	NC	NC	NC	HD2	HD5	HD8	HD11	HD14	$\overline{\text{WE}}$	CKE	DQS0	DQS3	DQM2	$\overline{\text{CS0}}$	NC	V _{DDM}
C	NC	NC	NC	NC	NC	NC	NC	NC	HD3	HD9	HD13	$\overline{\text{CAS}}$	$\overline{\text{RAS}}$	DQS1	DQM0	DQM3	$\overline{\text{CS1}}$	D25	D30	D24
D	NC	NC	NC	V _{DD}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDM}	V _{DDM}	V _{DDM}	V _{DDM}	V _{DDM}	V _{DDM}	GND	D27	D28	V _{DDM}
E	NC	NC	NC	V _{DD}	V _{DD}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDM}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DDM}	V _{DDM}	D31	D26	GND
F	NC	NC	NC	V _{DD}	V _{DD}	V _{DDIO}	GND	GND	GND	V _{DDM}	V _{DDM}	GND	GND	GND	V _{DD}	V _{DD}	V _{DD}	D29	D15	V _{DDM}
G	NC	NC	NC	V _{DD}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	GND	D13	GND
H	HA1	HA2	NC	V _{DD}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	D11	D12	D14
J	$\overline{\text{HREQ}}$	$\overline{\text{HACK}}$	HA3	V _{DD}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	V _{DDM}	D9	V _{DDM}	D10
K	$\overline{\text{HDS}}$	HDDS	HA0	V _{DD}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DD}	D8	GND	D0
L	HRW	$\overline{\text{HCS1}}$	$\overline{\text{HCS2}}$	V _{DD}	V _{DDIO}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DD}	D3	GND	D1
M	URXD	UTXD	SDA	V _{DD}	V _{DD}	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	D5	V _{DDM}	D2
N	V _{SSPLL}	SCL	CLKIN	V _{DD}	V _{DD}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	V _{DDM}	V _{REF}	D6	D4
P	V _{DDPLL}	TPSEL	$\overline{\text{PORESET}}$	V _{DD}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	V _{DDM}	D16	D17	D7
R	TEST0	EE0	TDO	V _{DD}	V _{DDIO}	V _{DDIO}	GND	V _{DDIO}	GND	GND	V _{DDM}	GND	V _{DDM}	GND	V _{DDM}	V _{DDM}	V _{DDM}	D18	D19	GND
T	$\overline{\text{HRESET}}$	TMS	NC	V _{DD}	V _{DD}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDM}	V _{DDM}	V _{DD}	V _{DDM}	V _{DDM}	V _{DD}	V _{DDM}	V _{DDM}	D22	D20	V _{DDM}
U	$\overline{\text{TRST}}$	TCK	NC	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DDM}	D23	D21	GND
V	TDI	NC	GPIA24	GPIA22	GPIA20	GPIA28	GPIA0	GPIA4	T0TCK	EVNT4	EVNT0	NC	BA0	A2	A5	A10	A11	A13	NC	V _{DDM}
W	H8BIT	GPIA26	GPIA23	GPIA19	GPIA27	GDPD4	GPIA1	GPIA3	T0TFS	T0RFS	EVNT2	EVNT1	NC	A3	A6	A7	A8	A12	V _{DDM}	GND
Y	GPIA25	GND	GPIA21	GPIA20	GPIA20	GPIA29	GPIA2	GPIA5	T0TD	T0RD	T0RCK	EVNT3	$\overline{\text{NMI}}$	BA1	A4	A0	A1	A9	GND	V _{DDM}

Note: The display is for mask set 1L44X. For mask set 1M88B, A16 is BM3 and B15 is BM2.

Figure 3. MSC7110 Molded Array Process-Ball Grid Array (MAP-BGA), Bottom View

1.2 Signal List By Ball Location

Table 1 lists the signals sorted by ball number and configuration.

Table 1. MSC7110 Signals by Ball Designator

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
A1		GND				
A2		GND				
A3		DQM1				
A4		DQS2				
A5		CK				
A6		$\overline{\text{CK}}$				
A7		GPIC7		GPOC7		HD15
A8		GPIC4		GPOC4		HD12
A9		GPIC2		GPOC2		HD10
A10		reserved				HD7
A11		reserved				HD6
A12		reserved				HD4
A13		reserved				HD1
A14		reserved				HD0
A15		GND				
A16 (1L44X)		NC				
A16 (1M88B)	BM3	GPID8		GPOD7		reserved
A17		NC				
A18		NC				
A19		NC				
A20		NC				
B1		V_{DDM}				
B2		NC				
B3		$\overline{\text{CS0}}$				
B4		DQM2				
B5		DQS3				
B6		DQS0				
B7		CKE				
B8		$\overline{\text{WE}}$				
B9		GPIC6		GPOC6		HD14
B10		GPIC3		GPOC3		HD11
B11		GPIC0		GPOC0		HD8
B12		reserved				HD5
B13		reserved				HD2
B14		NC				
B15 (1L44X)		NC				

Table 1. MSC7110 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
P1						D7
P2						D17
P3						D16
P4						V _{DDM}
P5						V _{DDM}
P6						V _{DDM}
P7						GND
P8						GND
P9						GND
P10						GND
P11						GND
P12						GND
P13						GND
P14						GND
P15						V _{DDIO}
P16						V _{DDIO}
P17						V _{DDC}
P18						PORESET
P19						TPSEL
P20						V _{DDPLL}
R1						GND
R2						D19
R3						D18
R4						V _{DDM}
R5						V _{DDM}
R6						V _{DDM}
R7						GND
R8						V _{DDM}
R9						GND
R10						V _{DDM}
R11						GND
R12						GND
R13						V _{DDIO}
R14						GND
R15						V _{DDIO}
R16						V _{DDIO}
R17						V _{DDC}
R18						TDO

Table 1. MSC7110 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
R19	reserved				EE0/DBREQ	
R20	TEST0					
T1	V _{DDM}					
T2	D20					
T3	D22					
T4	V _{DDM}					
T5	V _{DDM}					
T6	V _{DDC}					
T7	V _{DDM}					
T8	V _{DDM}					
T9	V _{DDC}					
T10	V _{DDM}					
T11	V _{DDM}					
T12	V _{DDIO}					
T13	V _{DDIO}					
T14	V _{DDIO}					
T15	V _{DDIO}					
T16	V _{DDC}					
T17	V _{DDC}					
T18	NC					
T19	TMS					
T20	HRESET					
U1	GND					
U2	D21					
U3	D23					
U4	V _{DDM}					
U5	V _{DDC}					
U6	V _{DDC}					
U7	V _{DDC}					
U8	V _{DDC}					
U9	V _{DDC}					
U10	V _{DDC}					
U11	V _{DDC}					
U12	V _{DDC}					
U13	V _{DDC}					
U14	V _{DDC}					
U15	V _{DDC}					
U16	V _{DDC}					

2.2 Recommended Operating Conditions

Table 3 lists recommended operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 3. Recommended Operating Conditions

Rating	Symbol	Value	Unit
Core supply voltage	V_{DDC}	1.14 to 1.26	V
Memory supply voltage	V_{DDM}	2.38 to 2.63	V
PLL supply voltage	V_{DDPLL}	1.14 to 1.26	V
I/O supply voltage	V_{DDIO}	3.14 to 3.47	V
Reference voltage	V_{REF}	1.19 to 1.31	V
Operating temperature range	T_J T_A	maximum: 105 minimum: -40	°C °C

2.3 Thermal Characteristics

Table 4 describes thermal characteristics of the MSC7110 for the MAP-BGA package.

Table 4. Thermal Characteristics for MAP-BGA Package

Characteristic	Symbol	MAP-BGA 17 × 17 mm ⁵		Unit
		Natural Convection	200 ft/min (1 m/s) airflow	
Junction-to-ambient ^{1, 2}	$R_{\theta JA}$	39	31	°C/W
Junction-to-ambient, four-layer board ^{1, 3}	$R_{\theta JA}$	23	20	°C/W
Junction-to-board ⁴	$R_{\theta JB}$	12		°C/W
Junction-to-case ⁵	$R_{\theta JC}$	7		°C/W
Junction-to-package-top ⁶	Ψ_{JT}	2		°C/W
Notes: 1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance. 2. Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal. 3. Per JEDEC JESD51-6 with the board horizontal. 4. Thermal resistance between the die and the printed circuit board per JEDEC JESD 51-8. Board temperature is measured on the top surface of the board near the package. 5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). 6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.				

Section 3.1, *Thermal Design Considerations* explains these characteristics in detail.

2.4 DC Electrical Characteristics

This section describes the DC electrical characteristics for the MSC7110.

Note: The leakage current is measured for nominal voltage values must vary in the same direction (for example, both V_{DDIO} and V_{DDC} vary by +2 percent or both vary by -2 percent).

Table 5. DC Electrical Characteristics

Characteristic	Symbol	Min	Typical	Max	Unit
Core and PLL voltage	V_{DDC} V_{DDPLL}	1.14	1.2	1.26	V
DRAM interface I/O voltage ¹	V_{DDM}	2.375	2.5	2.625	V
I/O voltage	V_{DDIO}	3.135	3.3	3.465	V
DRAM interface I/O reference voltage ²	V_{REF}	$0.49 \times V_{DDM}$	1.25	$0.51 \times V_{DDM}$	V
DRAM interface I/O termination voltage ³	V_{TT}	$V_{REF} - 0.04$	V_{REF}	$V_{REF} + 0.04$	V
Input high CLKIN voltage	V_{IHCLK}	2.4	3.0	3.465	V
DRAM interface input high I/O voltage	V_{IHM}	$V_{REF} + 0.28$	V_{DDM}	$V_{DDM} + 0.3$	V
DRAM interface input low I/O voltage	V_{ILM}	-0.3	GND	$V_{REF} - 0.18$	V
Input leakage current, $V_{IN} = V_{DDIO}$	I_{IN}	-1.0	0.09	1	μA
V_{REF} input leakage current	I_{VREF}	—	—	5	μA
Tri-state (high impedance off state) leakage current, $V_{IN} = V_{DDIO}$	I_{OZ}	-1.0	0.09	1	μA
Signal low input current, $V_{IL} = 0.4$ V	I_L	-1.0	0.09	1	μA
Signal high input current, $V_{IH} = 2.0$ V	I_H	-1.0	0.09	1	μA
Output high voltage, $I_{OH} = -2$ mA, except open drain pins	V_{OH}	2.0	3.0	—	V
Output low voltage, $I_{OL} = 5$ mA	V_{OL}	—	0	0.4	V
Typical core power ⁵ • at 200 MHz • at 266 MHz (mask set 1M88B only)	P_C	— —	222 293	— —	mW mW
Notes: 1. The value of V_{DDM} at the MSC7110 device must remain within 50 mV of V_{DDM} at the DRAM device at all times. 2. V_{REF} must be equal to 50% of V_{DDM} and track V_{DDM} variations as measured at the receiver. Peak-to-peak noise must not exceed $\pm 2\%$ of the DC value. 3. V_{TT} is not applied directly to the MSC7110 device. It is the level measured at the far end signal termination. It should be equal to V_{REF}. This rail should track variations in the DC level of V_{REF}. 4. Output leakage for the memory interface is measured with all outputs disabled, $0 V \leq V_{OUT} \leq V_{DDM}$. 5. The core power values were measured using a standard EFR pattern at typical conditions (25°C, 200 MHz or 266 MHz, 1.2 V core).					

Table 6 lists the DDR DRAM capacitance.

Table 6. DDR DRAM Capacitance

Parameter/Condition	Symbol	Max	Unit
Input/output capacitance: DQ, DQS	C_{IO}	30	pF
Delta input/output capacitance: DQ, DQS	C_{DIO}	30	pF
Note: These values were measured under the following conditions: • $V_{DDM} = 2.5 V \pm 0.125 V$ • $f = 1$ MHz • $T_A = 25^\circ C$ • $V_{OUT} = V_{DDM}/2$ • V_{OUT} (peak to peak) = 0.2 V			

2.5.2.1 PLL Multiplier Restrictions

There are two restrictions for correct usage of the PLL block:

- The input frequency to the PLL multiplier block (that is, the output of the divider) must be in the range 10.5–19.5 MHz.
- The output frequency of the PLL multiplier must be in the range 300–600 MHz.

When programming the PLL for a desired output frequency using the PLLDVF, PLLMLTF, and RNG fields, you must meet these constraints.

2.5.2.2 Division Factors and Corresponding CLKIN Frequency Range

The value of the PLLDVF field determines the allowable CLKIN frequency range, as shown in **Table 10**.

Table 10. CLKIN Frequency Ranges by Divide Factor Value

PLLDVF Field Value	Divide Factor	CLKIN Frequency Range	Comments
0x00	1	10.5 to 19.5 MHz	Pre-Division by 1
0x01	2	21 to 39 MHz	Pre-Division by 2
0x02	3	31.5 to 58.5 MHz	Pre-Division by 3
0x03	4	42 to 78 MHz	Pre-Division by 4
0x04	5	52.5 to 97.5 MHz	Pre-Division by 5
0x05	6	63 to 100 MHz	Pre-Division by 6
0x06	7	73.5 to 100 MHz	Pre-Division by 7
0x07	8	84 to 100 MHz	Pre-Division by 8
0x08	9	94.5 to 100 MHz	Pre-Division by 9
Note: The maximum CLKIN frequency is 100 MHz. Therefore, the PLLDVF value must be in the range from 1–9.			

2.5.2.3 Multiplication Factor Range

The multiplier block output frequency ranges depend on the input clock frequency as shown in **Table 11**.

Table 11. PLLMLTF Ranges

Multiplier Block (Loop) Output Range	Minimum PLLMLTF Value	Maximum PLLMLTF Value
$300 \leq [\text{Pre-Divided Clock} \times (\text{PLLMLTF} + 1)] \leq 600 \text{ MHz}$	300/Pre-Divided Clock	600/Pre-Divided Clock
Note: This table results from the allowed range for F_{Loop} . The minimum and maximum multiplication factors are dependent on the frequency of the Pre-Divided Clock.		

2.5.2.4 Allowed Core Clock Frequency Range

The frequency delivered to the core, extended core, and peripheral depends on the value of the CLKCTRL[RNG] bit as shown in **Table 12**.

Table 12. F_{VCO} Frequency Ranges

CLKCTRL[RNG] Value	Allowed Range of F_{VCO}
1	$300 \leq F_{\text{VCO}} \leq 600 \text{ MHz}$
0	$150 \leq F_{\text{VCO}} \leq 300 \text{ MHz}$
Note: This table results from the allowed range for F_{VCO} , which is F_{Loop} modified by CLKCTRL[RNG].	

This bit along with the CKSEL determines the frequency range of the core clock.

Table 16. Reset Actions for Each Reset Source

Reset Action/Reset Source	Power-On Reset (PORESET)	Hard Reset (HRESET)	Soft Reset (SRESET)
	External only	External or Internal (Software Watchdog or Bus Monitor)	JTAG Command: EXTEST, CLAMP, or HIGHZ
Configuration pins sampled (refer to Section 2.5.3.1 for details).	Yes	No	No
PLL and clock synthesis states Reset	Yes	No	No
HRESET Driven	Yes	Yes	No
Software watchdog and bus time-out monitor registers	Yes	Yes	Yes
Clock synthesis modules (STOPCTRL, HLTREQ, and HLTACK) reset	Yes	Yes	Yes
Extended core reset	Yes	Yes	Yes
Peripheral modules reset	Yes	Yes	Yes

2.5.3.1 Power-On Reset (PORESET) Pin

Asserting $\overline{\text{PORESET}}$ initiates the power-on reset flow. $\overline{\text{PORESET}}$ must be asserted externally for at least 16 CLKIN cycles after external power to the MSC7110 reaches at least $2/3 V_{DD}$.

2.5.3.2 Reset Configuration

The MSC7110 has two mechanisms for writing the reset configuration:

- From a host through the host interface (HDI16)
- From memory through the I²C interface

Five signal levels (see **Chapter 1** for signal description details) are sampled on $\overline{\text{PORESET}}$ deassertion to define the boot and operating conditions:

- BM[0–1]
- SWTE
- H8BIT
- HDSP

2.5.3.3 Reset Timing Tables

Table 17 and **Figure 4** describe the reset timing for a reset configuration write.

Table 17. Timing for a Reset Configuration Write

No.	Characteristics	Expression	Unit
1	Required external $\overline{\text{PORESET}}$ duration minimum	$16/F_{\text{CLKIN}}$	clocks
2	Delay from $\overline{\text{PORESET}}$ deassertion to $\overline{\text{HRESET}}$ deassertion	$521/F_{\text{CLKIN}}$	clocks
Note: Timings are not tested, but are guaranteed by design.			

Table 21. TDM Timing

No.	Characteristic	Expression	Min	Max	Units
307	TDMxTCK High to TDMxTD output valid		—	14.0	ns
308	TDMxTD hold time		2.0	—	ns
309	TDMxTCK High to TDMxTD output high impedance		—	10.0	ns
310	TDMxTFS/TDMxRFS output valid		—	13.5	ns
311	TDMxTFS/TDMxRFS output hold time		2.5	—	ns
Notes: 1. Output values are based on 30 pF capacitive load. 2. Inputs are referenced to the sampling that the TDM is programmed to use. Outputs are referenced to the programming edge they are programmed to use. Use of the rising edge or falling edge as a reference is programmable. Refer to the <i>MSC711x Reference Manual</i> for details. TDMxTCK and TDMxRCK are shown using the rising edge.					

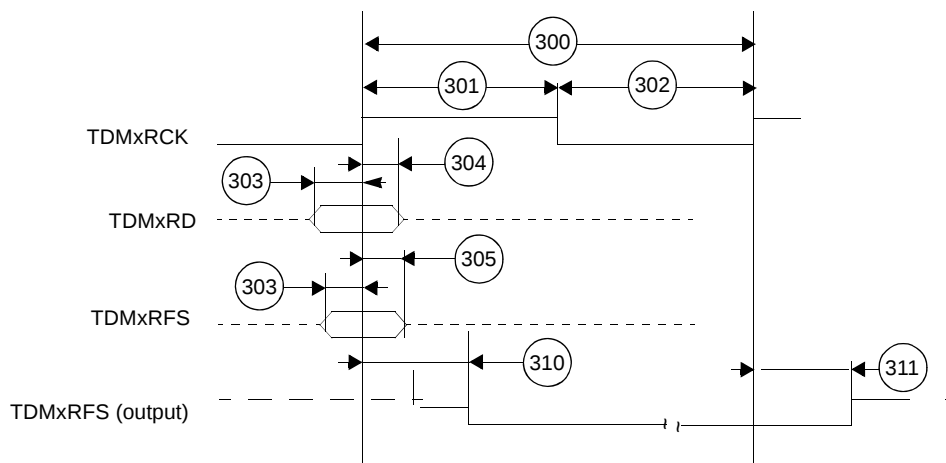


Figure 8. TDM Receive Signals

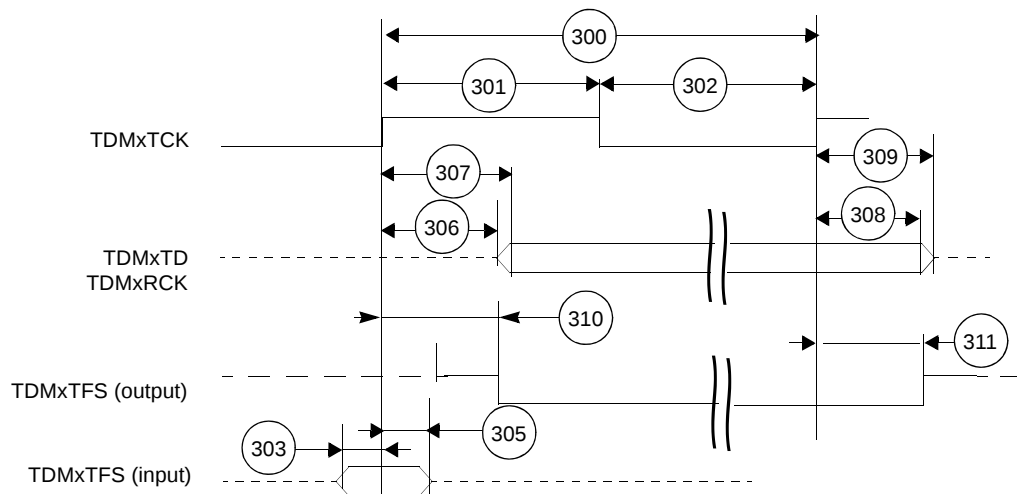


Figure 9. TDM Transmit Signals

2.5.6 HDI16 Signals

Table 22. Host Interface (HDI16) Timing^{1, 2}

No.	Characteristics ³	Mask Set 1L44X		Mask Set 1M88B		Unit
		Expression	Value	Expression	Value	
40	Host Interface Clock period	T_{HCLK}	Note 1	T_{CORE}	Note 1	ns

Table 22. Host Interface (HDI16) Timing^{1, 2} (continued)

No.	Characteristics ³	Mask Set 1L44X		Mask Set 1M88B		Unit
		Expression	Value	Expression	Value	
Notes:	1. $T_{HCLK} = 2/(\text{Core Clock})$. At 200 MHz, $T_{HCLK} = 10 \text{ ns}$. $T_{CORE} = \text{core clock period}$. At 266 MHz, $T_{CORE} = 3.75 \text{ ns}$. 2. In the timing diagrams below, the controls pins are drawn as active low. The pin polarity is programmable. 3. $V_{DD} = 3.3 \text{ V} \pm 0.15 \text{ V}$; $T_J = -40^{\circ}\text{C}$ to $+105^{\circ}\text{C}$, $C_L = 30 \text{ pF}$ for maximum delay timings and $C_L = 0 \text{ pF}$ for minimum delay timings. 4. The read data strobe is $\overline{HRD}/\overline{HRD}$ in the dual data strobe mode and $\overline{HDS}/\overline{HDS}$ in the single data strobe mode. 5. For 64-bit transfers, The "last data register" is the register at address 0x7, which is the last location to be read or written in data transfers. This is RX0/TX0 in the little endian mode (HBE = 0), or RX3/TX3 in the big endian mode (HBE = 1). 6. This timing is applicable only if a read from the "last data register" is followed by a read from the RXL, RXM, or RXH registers without first polling RXDF or HREQ bits, or waiting for the assertion of the $\overline{HREQ}/\overline{HREQ}$ signal. 7. This timing is applicable only if two consecutive reads from one of these registers are executed. 8. The write data strobe is $\overline{HWR}$ in the dual data strobe mode and $\overline{HDS}$ in the single data strobe mode. 9. The data strobe is host read ($\overline{HRD}/\overline{HRD}$) or host write ($\overline{HWR}/\overline{HWR}$) in the dual data strobe mode and host data strobe ($\overline{HDS}/\overline{HDS}$) in the single data strobe mode. 10. The host request is $\overline{HREQ}/\overline{HREQ}$ in the single host request mode and $\overline{HRRQ}/\overline{HRRQ}$ and $\overline{HTRQ}/\overline{HTRQ}$ in the double host request mode. $\overline{HRRQ}/\overline{HRRQ}$ is deasserted only when HOTX fifo is empty, $\overline{HTRQ}/\overline{HTRQ}$ is deasserted only if HORX fifo is full (treat as level Host Request). 11. Compute the value using the expression. 12. For mask set 1M88B, the read and write data strobe minimum deassertion width for non-"last data register" accesses in single and dual data strobe modes is based on timings 57 and 58.					

Figure 10 and Figure 11 show HDI16 read signal timing. Figure 12 and Figure 13 show HDI16 write signal timing.

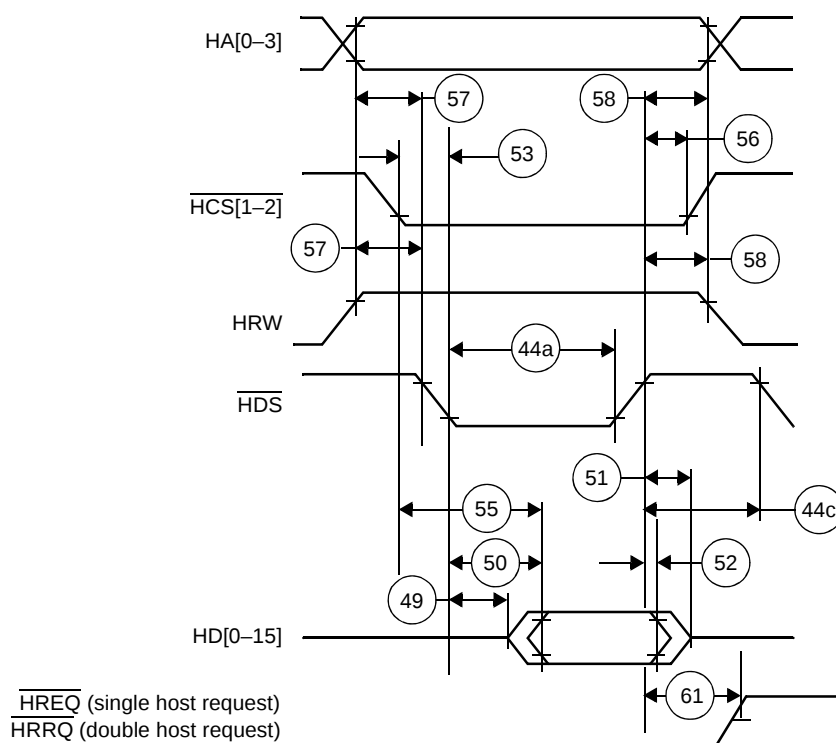


Figure 10. Read Timing Diagram, Single Data Strobe

2.5.7 I²C Timing

Table 23. I²C Timing

No.	Characteristic	Fast		Unit
		Min	Max	
450	SCL clock frequency	0	400	kHz
451	Hold time START condition	$(\text{Clock period}/2) - 0.3$	—	μs
452	SCL low period	$(\text{Clock period}/2) - 0.3$	—	μs
453	SCL high period	$(\text{Clock period}/2) - 0.1$	—	μs
454	Repeated START set-up time (not shown in figure)	$2 \times 1/F_{\text{BCK}}$	—	μs
455	Data hold time	0	—	μs
456	Data set-up time	250	—	ns
457	SDA and SCL rise time	—	700	ns
458	SDA and SCL fall time	—	300	ns
459	Set-up time for STOP	$(\text{Clock period}/2) - 0.7$	—	μs
460	Bus free time between STOP and START	$(\text{Clock period}/2) - 0.3$	—	μs

Note: SDA set-up time is referenced to the rising edge of SCL. SDA hold time is referenced to the falling edge of SCL. Load capacitance on SDA and SCL is 400 pF.

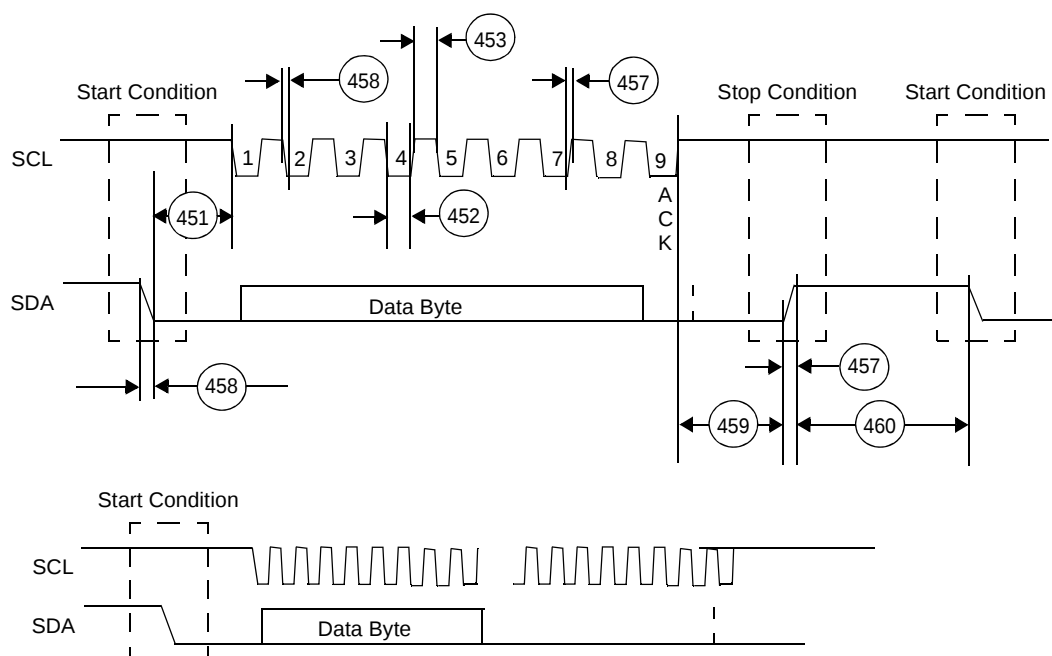


Figure 16. I²C Timing Diagram

2.5.8 UART Timing

Table 24. UART Timing

No.	Characteristics	Expression	Mask Set 1L44X		Mask Set 1M88B		Unit
			Min	Max	Min	Max	
—	Internal bus clock (APBCLK)	$F_{CORE}/2$	—	100	—	133	MHz
—	Internal bus clock period (1/APBCLK)	T_{APBCLK}	10.0	—	7.52	—	ns
400	URXD and UTXD inputs high/low duration	$16 \times T_{APBCLK}$	160.0	—	120.3	—	ns
401	URXD and UTXD inputs rise/fall time		—	5	—	5	ns
402	UTXD output rise/fall time		—	5	—	5	ns

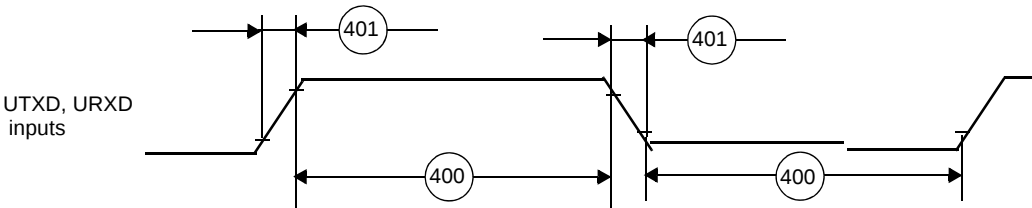


Figure 17. UART Input Timing

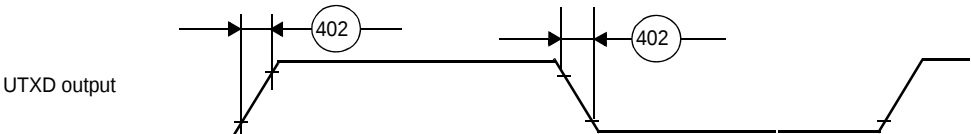


Figure 18. UART Output Timing

2.5.9 EE Timing

Table 25. EE0 Timing

Number	Characteristics	Type	Min
65	EE0 input to the core	Asynchronous	4 core clock periods
66	EE0 output from the core	Synchronous to core clock	1 core clock period

Notes:

1. The core clock is the SC1400 core clock. The ratio between the core clock and CLKOUT is configured during power-on-reset.
2. Configure the direction of the EE pin in the EE_CTRL register (see the *SC1400 Core Reference Manual* for details).
3. Refer to **Table 15** for details on EE pin functionality.

Figure 19 shows the signal behavior of the EE pin.

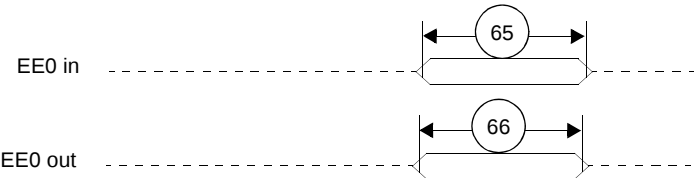


Figure 19. EE Pin Timing

2.5.12 JTAG Signals

Table 28. JTAG Timing

No.	Characteristics	All frequencies		Unit
		Min	Max	
700	TCK frequency of operation ($1/(T_C \times 3)$; maximum 22 MHz)	0.0	40.0	MHz
701	TCK cycle time	25.0	—	ns
702	TCK clock pulse width measured at $V_M = 1.6$ V	11.0	—	ns
703	TCK rise and fall times	0.0	3.0	ns
704	Boundary scan input data set-up time	5.0	—	ns
705	Boundary scan input data hold time	14.0	—	ns
706	TCK low to output data valid	0.0	20.0	ns
707	TCK low to output high impedance	0.0	20.0	ns
708	TMS, TDI data set-up time	5.0	—	ns
709	TMS, TDI data hold time	25.0	—	ns
710	TCK low to TDO data valid	0.0	24.0	ns
711	TCK low to TDO high impedance	0.0	10.0	ns
712	$\overline{\text{TRST}}$ assert time	100.0	—	ns

Note: All timings apply to OCE module data transfers as the OCE module uses the JTAG port as an interface.

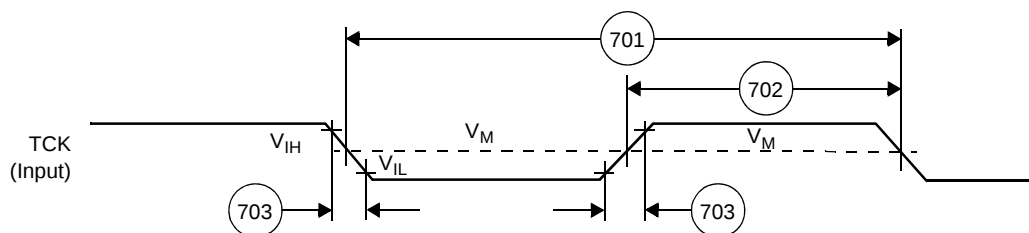


Figure 22. Test Clock Input Timing Diagram

3 Hardware Design Considerations

This section describes various areas to consider when incorporating the MSC7110 device into a system design.

3.1 Thermal Design Considerations

An estimation of the chip-junction temperature, T_J , in °C can be obtained from the following:

$$T_J = T_A + (R_{\theta JA} \times P_D) \quad \text{Eqn. 1}$$

where

T_A = ambient temperature near the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

$P_D = P_{INT} + P_{I/O}$ = power dissipation in the package (W)

$P_{INT} = I_{DD} \times V_{DD}$ = internal power dissipation (W)

$P_{I/O}$ = power dissipated from device on output pins (W)

The power dissipation values for the MSC7110 are listed in **Table 4**. The ambient temperature for the device is the air temperature in the immediate vicinity that would cool the device. The junction-to-ambient thermal resistances are JEDEC standard values that provide a quick and easy estimation of thermal performance. There are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. The value that more closely approximates a specific application depends on the power dissipated by other components on the printed circuit board (PCB). The value obtained using a single layer board is appropriate for tightly packed PCB configurations. The value obtained using a board with internal planes is more appropriate for boards with low power dissipation (less than 0.02 W/cm² with natural convection) and well separated components. Based on an estimation of junction temperature using this technique, determine whether a more detailed thermal analysis is required. Standard thermal management techniques can be used to maintain the device thermal junction temperature below its maximum. If T_J appears to be too high, either lower the ambient temperature or the power dissipation of the chip.

You can verify the junction temperature by measuring the case temperature using a small diameter thermocouple (40 gauge is recommended) or an infrared temperature sensor on a spot on the device case. Use the following equation to determine T_J :

$$T_J = T_T + (\Psi_{JT} \times P_D) \quad \text{Eqn. 2}$$

where

T_T = thermocouple (or infrared) temperature on top of the package (°C)

Ψ_{JT} = thermal characterization parameter (°C/W)

P_D = power dissipation in the package (W)

3.2.2.3 Case 3

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V) supply second.
3. Turn on the V_{DDM} (2.5 V) and V_{REF} (1.25 V) supplies simultaneously (third).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{DDM} (2.5 V) and V_{REF} (1.25 V) supplies simultaneously (first).
2. Turn off the V_{DDC} (1.2 V) supply second.
3. Turn of the V_{DDIO} (3.3 V) supply third (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down for V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down time for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 28** for relative timing for Case 3.

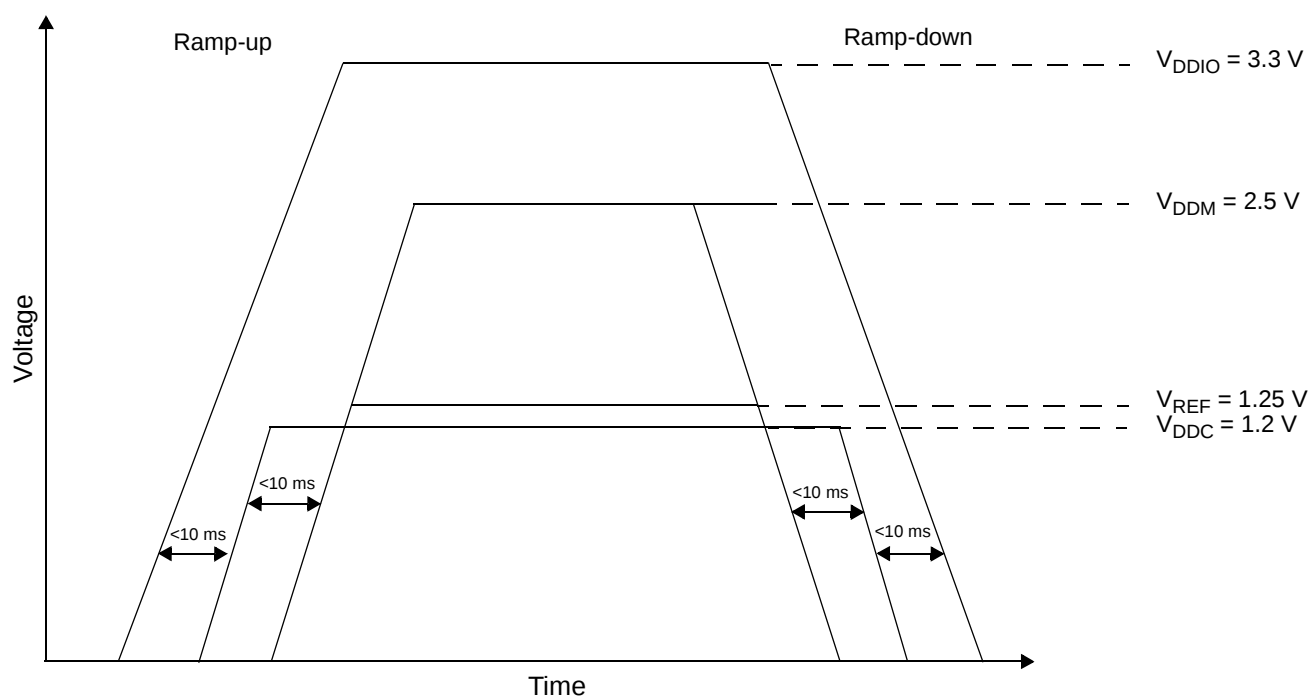


Figure 28. Voltage Sequencing Case 3

3.2.2.4 Case 4

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V), V_{DDM} (2.5 V), and V_{REF} (1.25 V) supplies simultaneously (second).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{DDC} (1.2 V), V_{REF} (1.25 V), and V_{DDM} (2.5 V) supplies simultaneously (first).
2. Turn of the V_{DDIO} (3.3 V) supply last.

Use the following guidelines:

- Make sure that the time interval between the ramp-up or ramp-down time for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 29** for relative timing for Case 4.

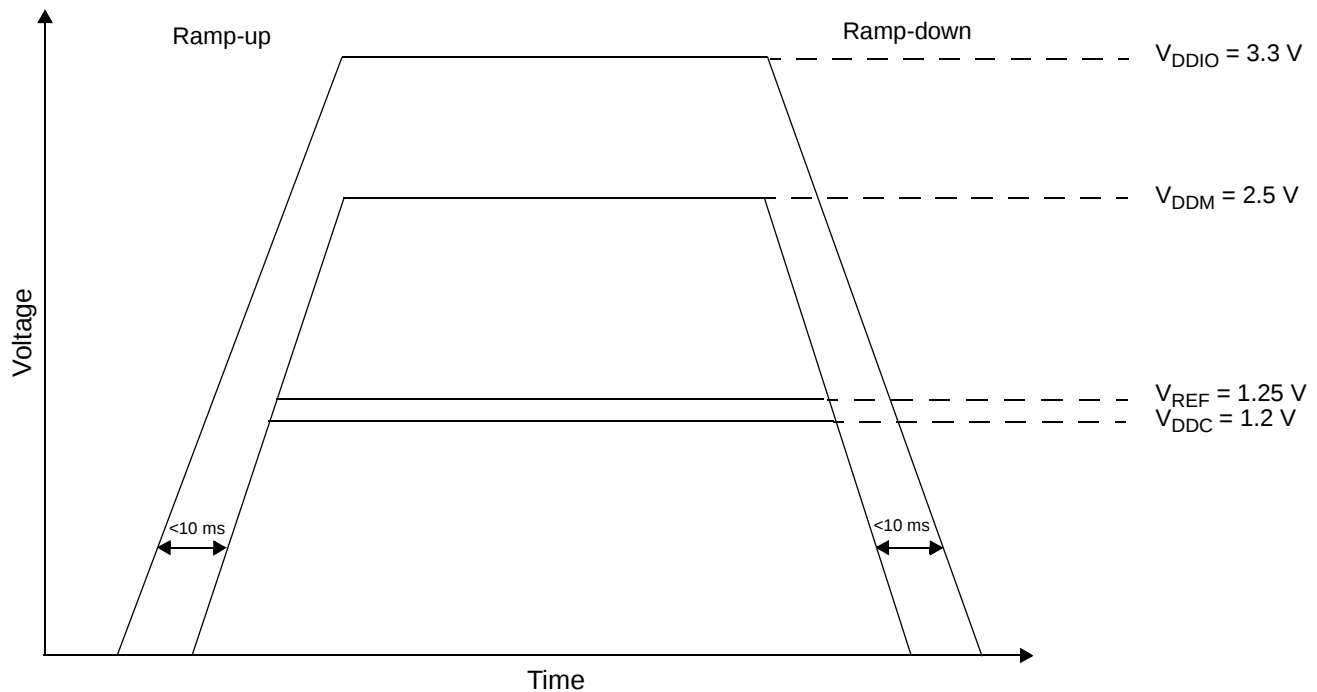


Figure 29. Voltage Sequencing Case 4

3.2.3 Power Planes

Each power supply pin (V_{DDC} , V_{DDM} , and V_{DDIO}) should have a low-impedance path to the board power supply. Each GND pin should be provided with a low-impedance path to ground. The power supply pins drive distinct groups of logic on the device. The MSC7110 V_{DDC} power supply pins should be bypassed to ground using decoupling capacitors. The capacitor leads and associated printed circuit traces connecting to device power pins and GND should be kept to less than half an inch per capacitor lead. A minimum four-layer board that employs two inner layers as power and GND planes is recommended. See **Section 3.5** for DDR Controller power guidelines.

3.2.4 Decoupling

Both the I/O voltage and core voltage should be decoupled for switching noise. For I/O decoupling, use standard capacitor values of $0.01\ \mu\text{F}$ for every two to three voltage pins. For core voltage decoupling, use two levels of decoupling. The first level should consist of a $0.01\ \mu\text{F}$ high frequency capacitor with low effective series resistance (ESR) and effective series inductance (ESL) for every two to three voltage pins. The second decoupling level should consist of two bulk/tantalum decoupling capacitors, one $10\ \mu\text{F}$ and one $47\ \mu\text{F}$, (with low ESR and ESL) mounted as closely as possible to the MSC7110 voltage pins. Additionally, the maximum drop between the power supply and the DSP device should be $15\ \text{mV}$ at $1\ \text{A}$.

3.2.5 PLL Power Supply Filtering

The MSC7110 V_{DDPLL} power signal provides power to the clock generation PLL. To ensure stability of the internal clock, the power supplied to this pin should be filtered with capacitors that have low and high frequency filtering characteristics. V_{DDPLL} can be connected to V_{DDC} through a $2\ \Omega$ resistor. V_{SSPLL} can be tied directly to the GND plane. A circuit similar to the one shown in **Figure 31** is recommended. The PLL loop filter should be placed as closely as possible to the V_{DDPLL} pin (which are located on the outside edge of the silicon package) to minimize noise coupled from nearby circuits. The $0.01\ \mu\text{F}$ capacitor should be closest to V_{DDPLL} , followed by the $0.1\ \mu\text{F}$ capacitor, the $10\ \mu\text{F}$ capacitor, and finally the $2\text{-}\Omega$ resistor to V_{DDC} . These traces should be kept short.

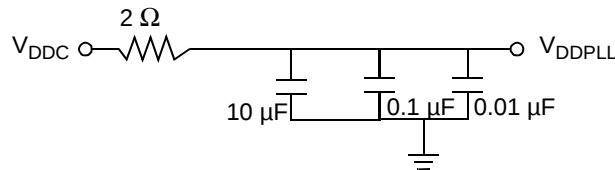


Figure 31. PLL Power Supply Filter Circuits

3.2.6 Power Consumption

You can reduce power consumption in your design by controlling the power consumption of the following regions of the device:

- *Extended core.* Use the SC1400 Stop and Wait modes by issuing a **stop** or **wait** instruction.
- *Clock synthesis module.* Disable the PLL, timer, watchdog, or DDR clocks or disable the CLK0 pin.
- *AHB subsystem.* Freeze or shut down the AHB subsystem using the GPSCTL[XBR_HRQ] bit.
- *Peripheral subsystem.* Halt the individual on-device peripherals such as the DDR memory controller, HDI16, TDM, UART, I²C, and timer modules.

For details, see the “Clocks and Power Management” chapter of the *MSC711x Reference Manual*.

3.5.3 General Routing

The general routing considerations for the DDR are as follows:

- All DDR signals must be routed next to a solid reference:
 - For data, next to solid ground planes.
 - For address/command, power planes if necessary.
- All DDR signals must be impedance controlled. This is system dependent, but typical values are 50–60 ohm.
- Minimize other cross-talk opportunities. As possible, maintain at least a four times the trace width spacing between all DDR signals to non-DDR signals.
- Keep the number of vias to a minimum to eliminate additional stubs and capacitance.
- Signal group routing priorities are as follows:
 - DDR clocks.
 - Route MVTT/MVREF.
 - Data group.
 - Command/address.
- Minimize data bit jitter by trace matching.

3.5.4 Routing Clock Distribution

The DDR clock distribution considerations are as follows:

- DDR controller supports six clock pairs:
 - 2 DIMM modules.
 - Up to 36 discrete chips.
- For route traces as for any other differential signals:
 - Maintain proper difference pair spacing.
 - Match pair traces within 25 mm.
- Match all clock traces to within 100 mm.
- Keep all clocks equally loaded in the system.
- Route clocks on inner critical layers.

3.5.5 Data Routing

The DDR data routing considerations are as follows:

- Route each data group (8-bits data + DQS + DM) on the same layer. Avoid switching layers within a byte group.
- Take care to match trace lengths, which is extremely important.
- To make trace matching easier, let adjacent groups be routed on alternate critical layers.
- Pin swap bits within a byte group to facilitate routing (discrete case).
- Tight trace matching is recommended within the DDR data group. Keep each 8-bit datum and its DM signal within ± 25 mm of its respective strobe.
- Minimize lengths across the entire DDR channel:
 - Between all groups maintain a delta of no more than 500 mm.
 - Allows greater flexibility in the design for readjustments as needed.
- DDR data group separation:
 - If stack-up allows, keep DDR data groups away from the address and control nets.
 - Route address and control on separate critical layers.
 - If resistor networks (RNs) are used, attempt to keep data and command lines in separate packages.

5 Package Information

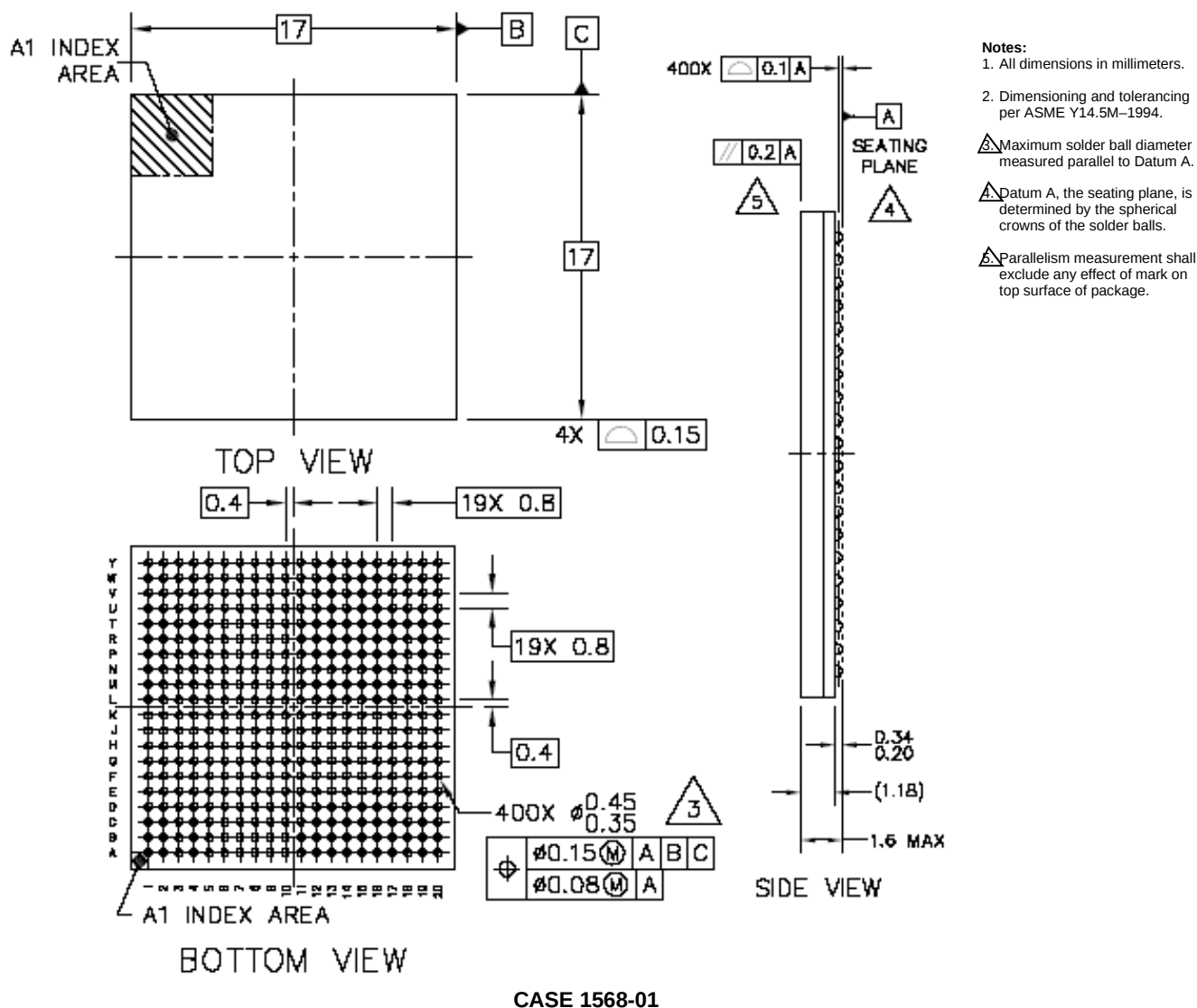


Figure 34. MSC7110 Mechanical Information, 400-pin MAP-BGA Package

6 Product Documentation

- *MSC711x Reference Manual* (MSC711xRM). Includes functional descriptions of the extended cores and all the internal subsystems including configuration and programming information.
- *Application Notes*. Cover various programming topics related to the StarCore DSP core and the MSC7110 device.
- *SC140/SC1400 DSP Core Reference Manual*. Covers the SC140 and SC1400 core architecture, control registers, clock registers, program control, and instruction set.